

isc N-Channel MOSFET Transistor

TK7A80W

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valanche tested			1 2 3	3		2.Drain 3.Sour	n rce
RITION			• B	-	- C -		
ng Voltage Regulators .UTE MAXIMUM RATINGS(Ta=25°	C)		F OOO	Ģ	-5-	v v	⊖° [
PARAMETER	VALUE	UNIT					
Drain-Source Voltage	800	V	L	¥.	- R	* 1	ţΠ.
Gate-Source Voltage	±20	V		ĸ			
Drain Current-Continuous	6.5	А	D		J	Ų	U U
Drain Current-Single Pulsed	26	A		DIM	MIN	m MAX	
Total Dissipation @T _C =25℃	35	W		A B	14.95 10.00	15.05 10.10	
Max. Operating Junction Temperature	150	°C		D	0.75	0.90	
Storage Temperature	-55~150	°C		Н	3.70	3.90	
IAL CHARACTERISTICS		L		K L N	13.4 1.10 5.00	13.6 1.30 5.20	
PARAMETER	МАХ	UNIT		R	2.20	2.40	
				S	2.65	2.90	
	ain-source on-resistance: on) ≤0.95Ω. mement mode: 3.0 to 4.0V (VDs = 10 V, ID=0.28mA valanche tested m Lot-to-Lot variations for robust de pance and reliable operation RITION ng Voltage Regulators LUTE MAXIMUM RATINGS(T_a=25° PARAMETER Drain-Source Voltage Gate-Source Voltage Drain Current-Continuous Drain Current-Single Pulsed Total Dissipation @Tc=25°C Max. Operating Junction Temperature Storage Temperature Storage Temperature	ain-source on-resistance: on) ≤0.95Ω. rement mode: 3.0 to 4.0V (Vos = 10 V, lo=0.28mA) valanche tested m Lot-to-Lot variations for robust device hance and reliable operation RITION ng Voltage Regulators LUTE MAXIMUM RATINGS(Ta=25°C) PARAMETER VALUE Drain-Source Voltage 800 Gate-Source Voltage 800 Gate-Source Voltage 1±20 Drain Current-Continuous 6.5 Drain Current-Single Pulsed 26 Total Dissipation @Tc=25°C 35 Max. Operating Junction Temperature 150 Storage Temperature -55~150	ain-source on-resistance: on) ≤0.95Ω. sement mode: 3.0 to 4.0V (VDs = 10 V, ID=0.28mA) valanche tested m Lot-to-Lot variations for robust device ance and reliable operation XITION ng Voltage Regulators VALUE UNIT Drain-Source Voltage $VALUE$ UNIT Drain-Source Voltage ± 20 V Gate-Source Voltage ± 20 V Drain Current-Continuous 6.5 A Drain Current-Continuous 6.5 A Drain Current-Single Pulsed 26 A Total Dissipation @Tc=25°C Max. Operating Junction Temperature 150 °C Storage Temperature $-55~150$ °C	ain-source on-resistance: on) ≤0.95Ω. seement mode: 3.0 to 4.0V (Vbs = 10 V, lb=0.28mA) valanche tested m Lot-to-Lot variations for robust device ance and reliable operation RITION ng Voltage Regulators LUTE MAXIMUM RATINGS(Ta=25°C) PARAMETER VALUE UNIT Drain-Source Voltage 800 V Gate-Source Voltage 800 V Gate-Source Voltage 26 A Drain Current-Continuous 6.5 A Drain Current-Single Pulsed 26 A Total Dissipation @Tc=25°C 35 W Max. Operating Junction Temperature 150 °C Storage Temperature 55~150 °C	the source on-resistance: b) $\leq 0.95 \Omega$. the ment mode: 3.0 to 4.0V (Vbs = 10 V, lb=0.28mA) valanche tested m Lot-to-Lot variations for robust device thance and reliable operation RITION ng Voltage Regulators LUTE MAXIMUM RATINGS(Ta=25°C) PARAMETER VALUE UNIT Drain-Source Voltage 800 V Gate-Source Voltage 1 ± 20 V Drain Current-Continuous 6.5 A Drain Current-Single Pulsed 26 A Total Dissipation @Tc=25°C 35 W Max. Operating Junction Temperature 150 °C Storage Temperature $-55-150$ °C HAL CHARACTERISTICS PARAMETER MAX UNIT	ain-source on-resistance: on $) \le 0.95\Omega$. sement mode: 3.0 to 4.0V (Vbs = 10 V, lp=0.28mA) valanche tested m Lot-to-Lot variations for robust device hance and reliable operationminustance: TOTONUTION ng Voltage RegulatorsLUTE MAXIMUM RATINGS(Ta=25°C)PARAMETERVALUEUNITDrain-Source Voltage800VGate-Source Voltage ± 20 VDrain Current-Continuous 6.5 ADrain Current-Single Pulsed26ATotal Dissipation @Tc=25°C35WMax. Operating Junction Temperature150°CStorage Temperature150CAL CHARACTERISTICSPARAMETERMAXUNIT	ain-source on-resistance: on) $\leq 0.95 \Omega$. we ment mode: $3.0 to 4.0V$ (Vos = 10 V, ID=0.28mA) valanche tested m Lot-to-Lot variations for robust device hance and reliable operationpin 1.Gate 2.Drain 3.Source TO-220F pRITION ng Voltage RegulatorsLUTE MAXIMUM RATINGS(Ta=25°C)PARAMETERVALUEUNITDrain-Source Voltage ± 20 VGate-Source Voltage ± 20 VDrain Current-Continuous 6.5 ADrain Current-Single Pulsed 26 ATotal Dissipation @Tc=25°C 35 WMax. Operating Junction Temperature 150 °CKI CHARACTERISTICSPARAMETERMAXUNIT



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ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =10mA	800			V
$V_{GS(th)}$	Gate Threshold Voltage	V _{DS} =10V; I _D =0.28mA	3.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =3.3A			950	mΩ
lgss	Gate-Source Leakage Current	V _{GS} = ±20V;V _{DS} = 0V			±1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =800V; V _{GS} = 0V			10	μA
V _{SDF}	Diode forward voltage	I _{DR} =6.5A, V _{GS} = 0 V			1.7	V



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